1SS77WS

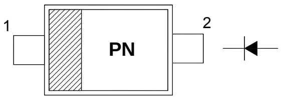
SILICON EPITAXIAL PLANAR

BAND SWITCHING DIODE

For band switching application

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode



Top View
Marking Code: "**PN**"
Simplified outline SOD-323 and symbol

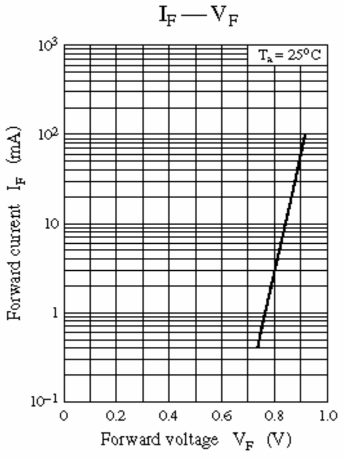
Absolute Maximum Ratings (T_a = 25 °C)

Parameter	Symbol	Value	Unit
Reverse Voltage	V_R	35	V
Forward Current	I_F	100	mA
Operating Ambient Temperature [1]	T_{opr}	- 25 to + 85	°C
Storage Temperature Range	T_s	- 55 to + 150	°C

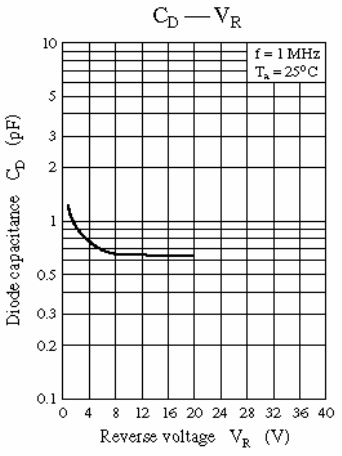
[1] Maximum ambient temperature during operation

Characteristics at T_a = 25 °C

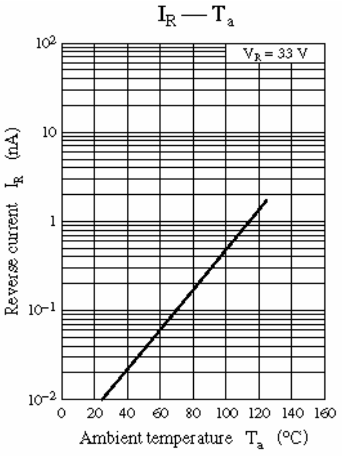
Parameter	Symbol	Max.	Unit
Forward Voltage at I_F = 100 mA	V_F	1	V
Reverse Current at V_R = 33 V	I_R	0.1	µA
Diode Capacitance at V_R = 6 V, f = 1 MHz	C_D	1.2	pF
Forward Dynamic Resistance at I_F = 2 mA, f = 100 MHz	r_f	0.85	Ω



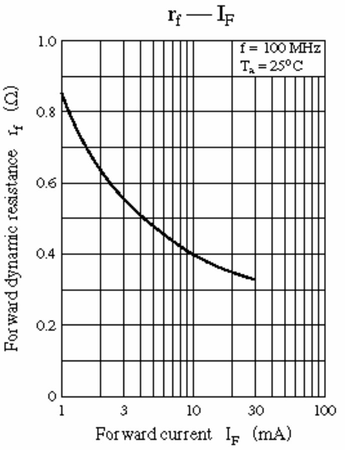
I_F — V_F



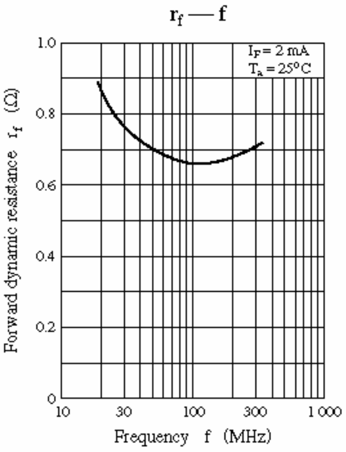
C_D — V_R



I_R — T_a



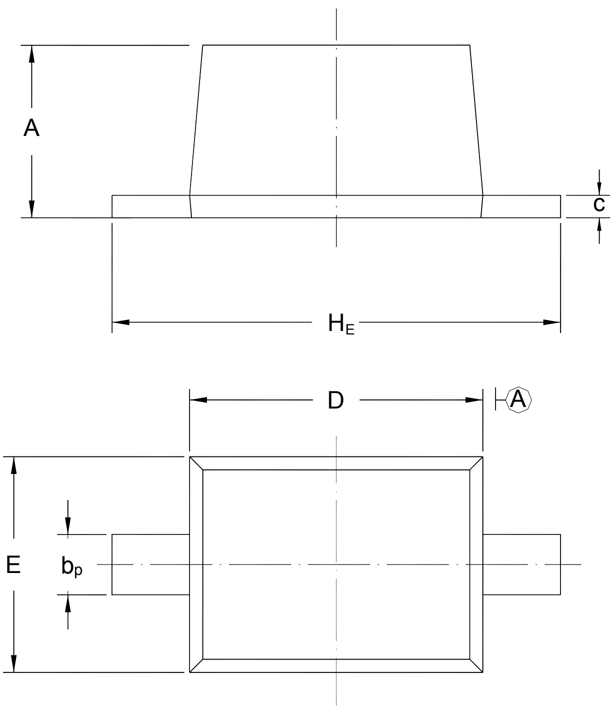
r_f — I_F



r_f — f

PACKAGE OUTLINE

Plastic surface mounted package; 2 leads **SOD-323**



UNIT	A	b_p	C	D	E	H_E
mm	1.10 0.80	0.40 0.25	0.15 0.00	1.80 1.60	1.35 1.15	2.80 2.30